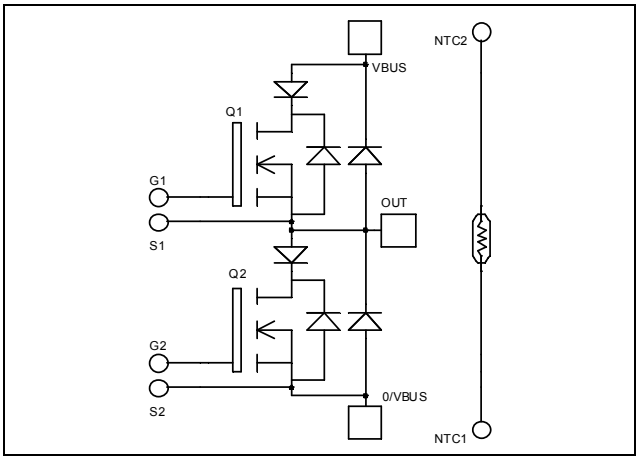
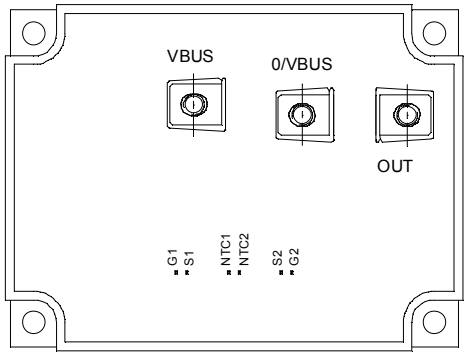
APTM50AM19ST

Phase leg Schottky Series & parallel diodes MOSFET Power Module

V_{DSS} = 500V
R_{DSon} = 19mΩ max @ Tj = 25°C
I_D = 170A @ Tc = 25°C





Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7® MOSFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals for signal and M5 for power for easy PCB mounting

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		500	V
I_D	Continuous Drain Current	T_c = 25°C	170	A
		T_c = 80°C	125	
I_{DM}	Pulsed Drain current		360	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		19	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	1250	W
I_{AR}	Avalanche current (repetitive and non repetitive)		46	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
BV_{DSS}	Drain - Source Breakdown Voltage	V_{GS} = 0V, I_D = 500µA		500			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 500V	T_j = 25°C			500	µA
		V_{GS} = 0V, V_{DS} = 400V	T_j = 125°C			2000	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 85A				19	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 10mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±200	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		22.4		nF
C_{oss}	Output Capacitance			4.8		
C_{rss}	Reverse Transfer Capacitance			0.36		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 250V I_D = 170A		492		nC
Q_{gs}	Gate – Source Charge			132		
Q_{gd}	Gate – Drain Charge			260		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 333V I_D = 170A R_G = 1Ω		18		ns
T_r	Rise Time			35		
$T_{d(off)}$	Turn-off Delay Time			87		
T_f	Fall Time			77		
E_{on}	Turn-on Switching Energy ❶	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 333V I_D = 170A, R_G = 1Ω		3020		µJ
E_{off}	Turn-off Switching Energy ❷			2904		
E_{on}	Turn-on Switching Energy ❶	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 333V I_D = 170A, R_G = 1Ω		4964		µJ
E_{off}	Turn-off Switching Energy ❷			3384		

Series Schottky diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	T_c = 85°C		120		A
V_F	Diode Forward Voltage	I_F = 120A			0.77		V
		I_F = 120A	T_j = 125°C		0.62		

❶ E_{on} includes diode reverse recovery.
❷ In accordance with JEDEC standard JESD24-1.

Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	T_c = 70°C		180		A
V_F	Diode Forward Voltage	I_F = 180A			1.6	1.8	V
		I_F = 360A			1.9		
		I_F = 180A	T_j = 125°C		1.4		
t_{rr}	Reverse Recovery Time	I_F = 180A V_R = 400V di/dt = 600A/µs	T_j = 25°C		130		ns
			T_j = 125°C		170		
Q_{rr}	Reverse Recovery Charge	I_F = 180A V_R = 400V di/dt = 600A/µs	T_j = 25°C		660		nC
			T_j = 125°C		2760		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case	Transistor				0.1	°C/W
		Series Diode				0.5	
		Parallel diode				0.32	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M5	2		3.5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					620	g

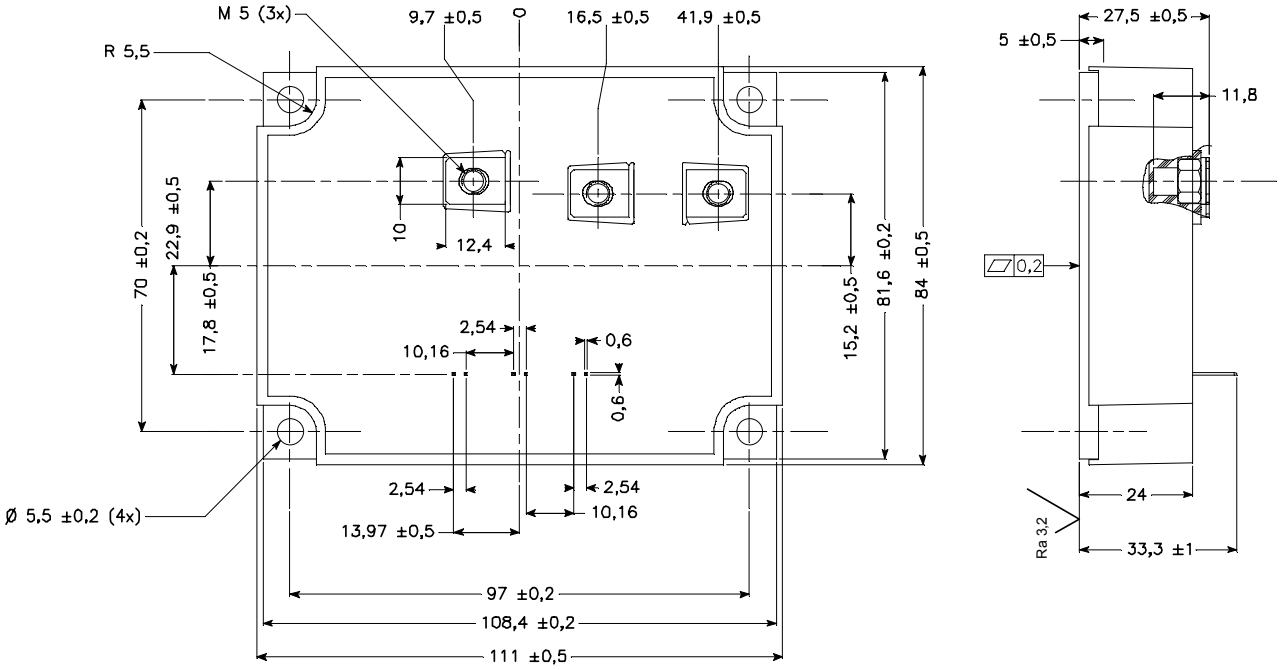
Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		68		kΩ
$B_{25/85}$	T_{25} = 298.16 K		4080		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

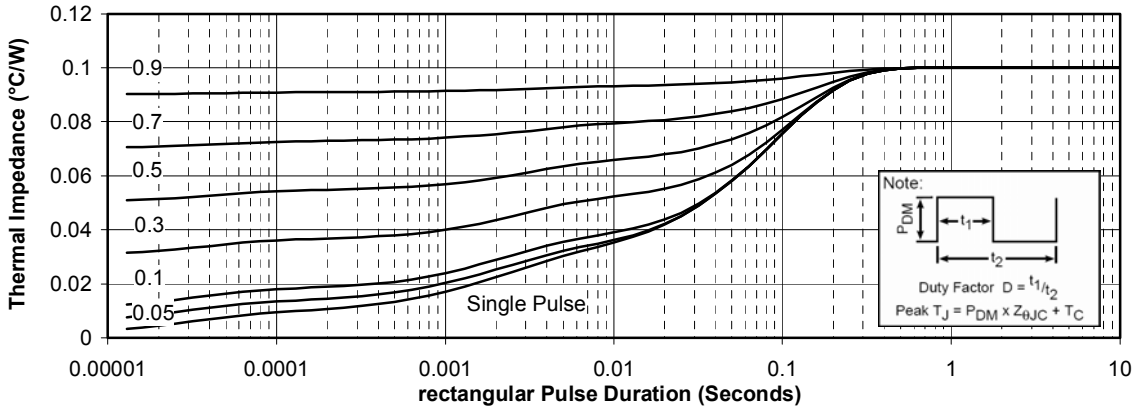
T: Thermistor temperature
R_T: Thermistor value at T

Package outline

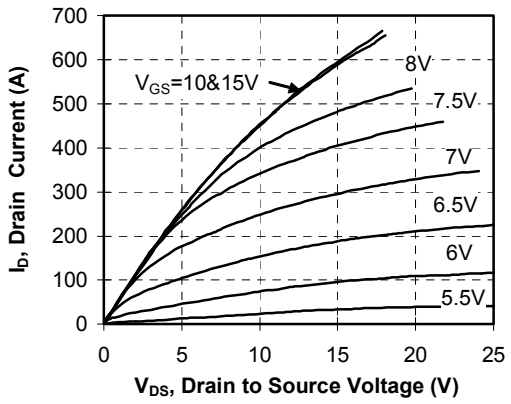


Typical Performance Curve

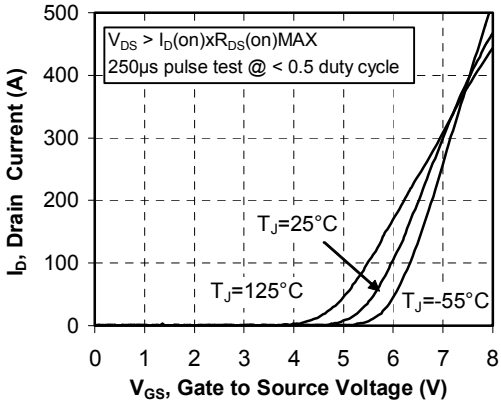
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



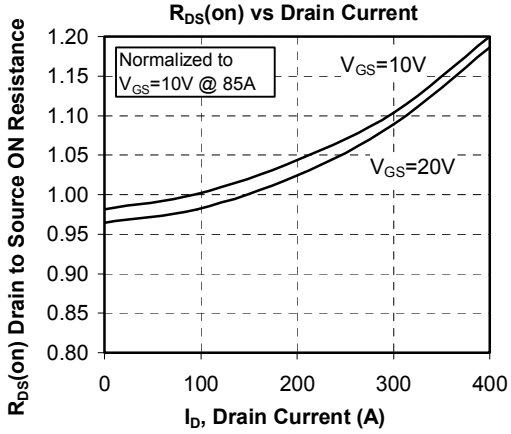
Low Voltage Output Characteristics



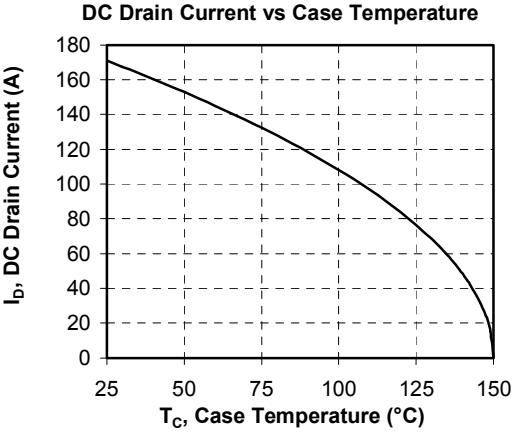
Transfert Characteristics



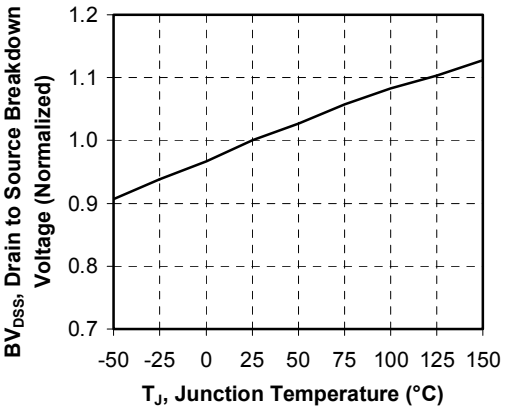
R_{DS}(on) vs Drain Current



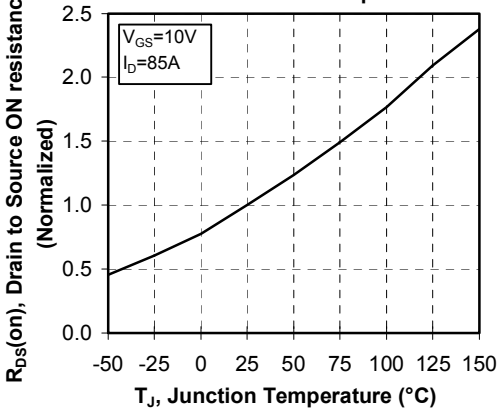
DC Drain Current vs Case Temperature



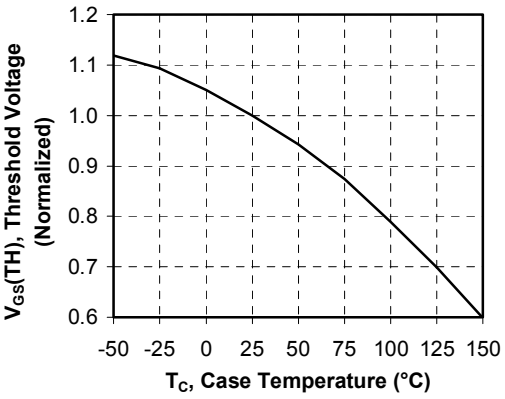
Breakdown Voltage vs Temperature



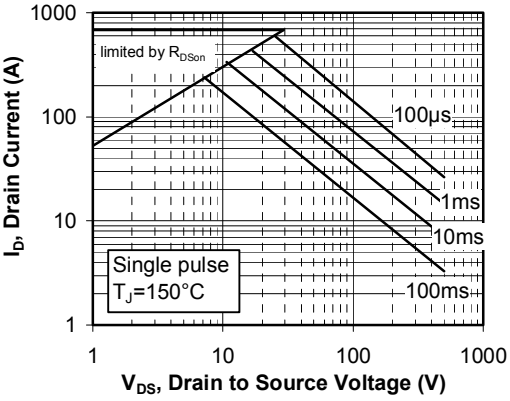
ON resistance vs Temperature



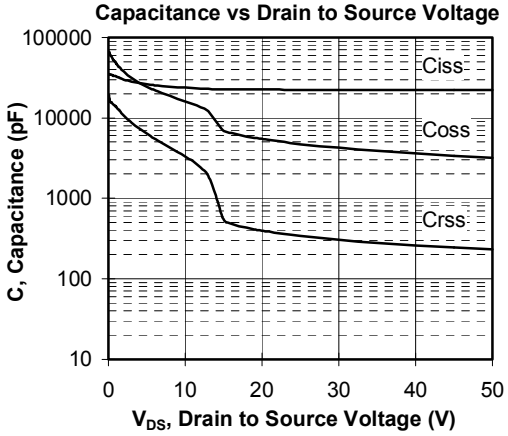
Threshold Voltage vs Temperature



Maximum Safe Operating Area



Capacitance vs Drain to Source Voltage



Gate Charge vs Gate to Source Voltage